THE DATASHEET OF

CAS120M12BM2

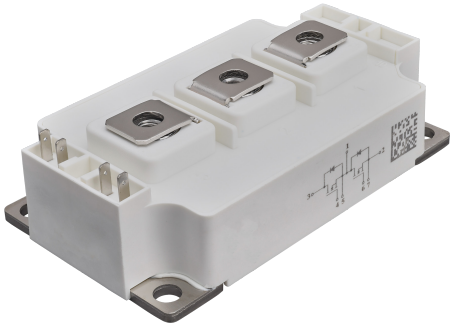
CAS120M12BM2

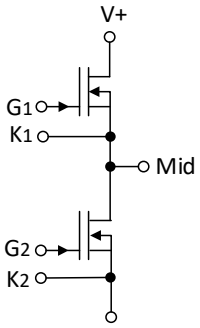
V_{DS}	**1200 V**
I_{DS}	**120 A**

1200 V, 120 A All-Silicon Carbide
High Performance, Switching Optimized, Half-Bridge Module

Technical Features

- Industry Standard 62 mm Footprint
- Ultra-Low Loss, High-Frequency Operation
- Zero Reverse Recovery from Diodes
- Zero Turn-off Tail Current from MOSFET
- Normally-off, Fail-safe Device Operation
- Copper Baseplate and Aluminum Nitride Insulator





Applications

- Railway & Traction
- Solar & Renewable Energy
- EV Charging
- Industrial Automation & Testing

System Benefits

- Fast Time-to-Market with Minimal Development Required for Transition from 62 mm IGBT Packages
- Increased System Efficiency, due to Low Switching & Conduction Losses of SiC

Key Parameters

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	Note
Drain-Source Voltage	V_{DS}			1200	V	T_C = 25 °C	
Gate-Source Voltage, Maximum Value	$V_{GS(max)}$	-10		+25		Transient	Note 1 Fig. 33
Gate-Source Voltage, Recommended	$V_{GS(op)}$		-5/+20			Static	
DC Continuous Drain Current	I_D		200		A	V_{GS} = 20 V, T_C = 25 °C, T_{VJ} ≤ 150 °C	Notes 2, 3 Fig. 21
			144			V_{GS} = 20 V, T_C = 90 °C, T_{VJ} ≤ 150 °C	
DC Source-Drain Current (Schottky Diode)	$I_{SD(SD)}$		460			V_{GS} = -5 V, T_C = 25 °C, T_{VJ} ≤ 150 °C	
Pulsed Drain-Source Current	I_{DM}		480			t_{Pmax} limited by T_{VJmax} V_{GS} = 20 V, T_C = 25 °C	
Power Dissipation	P_D		1000		W	T_C = 25 °C, T_{VJ} ≤ 150 °C	Note 4 Fig. 21
Virtual Junction Temperature	$T_{VJ(op)}$	-40		150	°C	Operation	

Note (1): Recommended turn-on gate voltage is 20 V with ±5 % regulation tolerance
Note (2): Current limit at T_C = 90 °C calculated by $I_{D(max)} = \sqrt{(P_D/R_{DS(typ)}(T_{VJ(max)}, I_{D(max)}))}$
Note (3): Verified by design
Note (4): $P_D = (T_{VJ} - T_C)/R_{TH(JC,typ)}$

4600 Silicon Drive | Durham, NC 27703 | Tel: +1.919.313.5300 | wolfspeed.com/power

MOSFET Characteristics (Per Position) (T_{VJ} = 25 °C Unless Otherwise Specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	Note
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200			V	V_{GS} = 0 V, T_{VJ} = -40 °C	
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.6			V_{DS} = V_{GS}, I_D = 6 mA	
Zero Gate Voltage Drain Current	I_{DSS}		450	3000	µA	V_{GS} = 0 V, V_{DS} = 1200 V	
Gate-Source Leakage Current	I_{GSS}			1.5		V_{GS} = 20 V, V_{DS} = 0 V	
Drain-Source On-State Resistance (Devices Only)	$R_{DS(on)}$		13.0	16.0	mΩ	V_{GS} = 20 V, I_D = 120 A	Fig. 2 Fig. 3
			23.0			V_{GS} = 20 V, I_D = 120 A, T_{VJ} = 150 °C	
Transconductance	g_{fs}		57.4		S	V_{DS} = 20 V, I_{DS} = 120 A	Fig. 4
			54.4			V_{DS} = 20 V, I_{DS} = 120 A, T_{VJ} = 150 °C	
Turn-On Switching Energy, T_{VJ} = 25 °C T_{VJ} = 125 °C T_{VJ} = 150 °C	E_{ON}		1.39 1.24 1.19		mJ	V_{DS} = 600 V, I_D = 120 A, V_{GS} = -5 V/+20 V, $R_{G(ext)}$ = 2.5 Ω, L = 22.5 µH	Fig. 11 Fig. 13
Turn-Off Switching Energy, T_{VJ} = 25 °C T_{VJ} = 125 °C T_{VJ} = 150 °C	E_{OFF}		0.86 0.84 0.85				
Internal Gate Resistance	$R_{G(int)}$		1.8		Ω	V_{AC} = 25 mV, f = 100 kHz	
Input Capacitance	C_{iss}		6.47		nF	V_{GS} = 0 V, V_{DS} = 800 V, V_{AC} = 25 mV, f = 200 kHz	Fig. 9
Output Capacitance	C_{oss}		0.98				
Reverse Transfer Capacitance	C_{rss}		43.8		pF		
Gate to Source Charge	Q_{GS}		97		nC	V_{DS} = 800 V, V_{GS} = -5 V/+20 V I_D = 120 A Per IEC60747-8-4 pg 21	
Gate to Drain Charge	Q_{GD}		118				
Total Gate Charge	Q_G		378				
FET Thermal Resistance, Junction to Case	$R_{th\ JC}$		0.125	0.135	°C/W		Fig. 17

Diode Characteristics (Per Position) (T_{VJ} = 25 °C Unless Otherwise Specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	Note
Diode Forward Voltage	V_F		1.53		V	V_{GS} = -5 V, I_F = 120 A, T_{VJ} = 25 °C	Fig. 7
			1.92			V_{GS} = -5 V, I_F = 120 A, T_{VJ} = 150 °C	
Reverse Recovery Time	t_{RR}		21		ns	V_{GS} = -5 V, I_{SD} = 120 A, V_R = 600 V di_F/dt = 12.5 A/ns, T_J = 150 °C	Fig. 32
Reverse Recovery Charge	Q_{RR}		2.2		µC		
Peak Reverse Recovery Current	I_{RRM}		173		A		
Diode Energy T_{VJ} = 25 °C T_{VJ} = 125 °C T_{VJ} = 150 °C	E_{rr}		0.75 0.86 0.89		mJ	V_{DS} = 600 V, I_D = 120 A, V_{GS} = -5 V/+20 V, $R_{G(ext)}$ = 2.5 Ω, L = 22.5 µH	Fig. 14 Note 5
Diode Thermal Resistance, Junction to Case	$R_{th\ JC}$		0.108	0.115	°C/W		Fig. 18

Note (5): SiC Schottky diodes do not have reverse recovery energy but still contribute capacitive energy

Module Physical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Package Resistance, M1	R_{1-2}		0.60		μΩ	T_C = 125 °C, Note: 6
Package Resistance, M2	R_{2-3}		0.51			T_C = 125 °C, Note: 6
Stray Inductance	L_{Stray}		12.9		nH	Between Terminals 1 and 3
Case Temperature	T_C	-40		125	°C	
Weight	W		290		g	
Mounting Torque	M_S	4	5	5.5	N-m	Baseplate, M6-1.0 Bolts
		4	5	5.5		Power Terminals, M6-1.0 Bolts
Case Isolation Voltage	V_{isol}	5			kV	AC, 50 Hz, 1 min
Clearance Distance		9			mm	Terminal to Terminal
		30				Terminal to Baseplate
Creepage Distance		30				Terminal to Terminal
		40				Terminal to Baseplate

Note (6): Total Effective Resistance (Per Switch Position) = MOSFET $R_{DS(on)}$ + Switch Position Package Resistance

Typical Performance

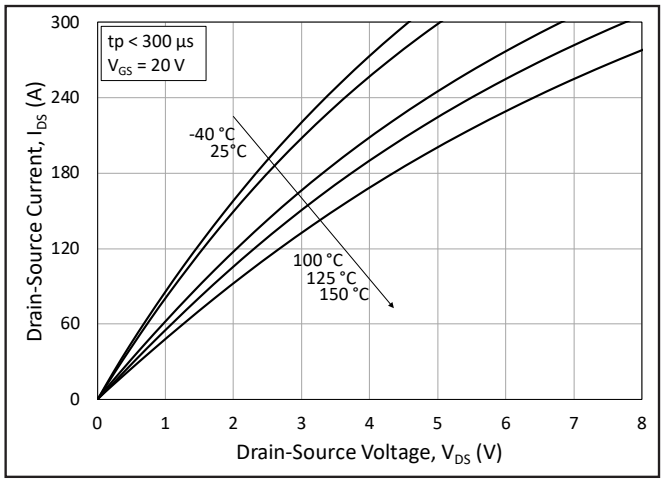


Figure 1. Output Characteristics for Various Junction Temperatures

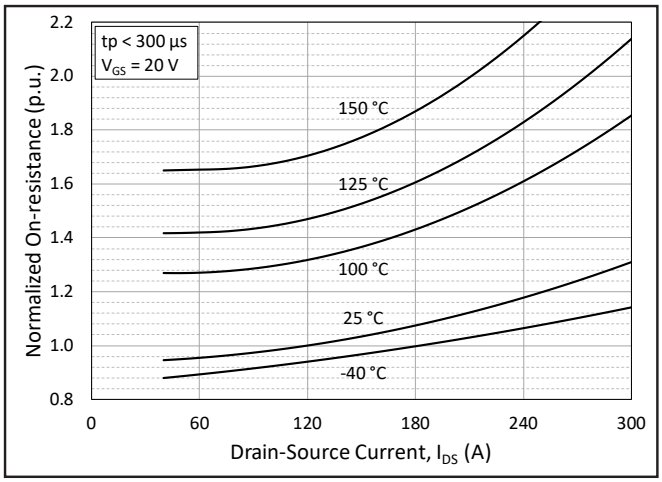


Figure 2. Normalized On-State Resistance vs. Drain Current for Various Junction Temperatures

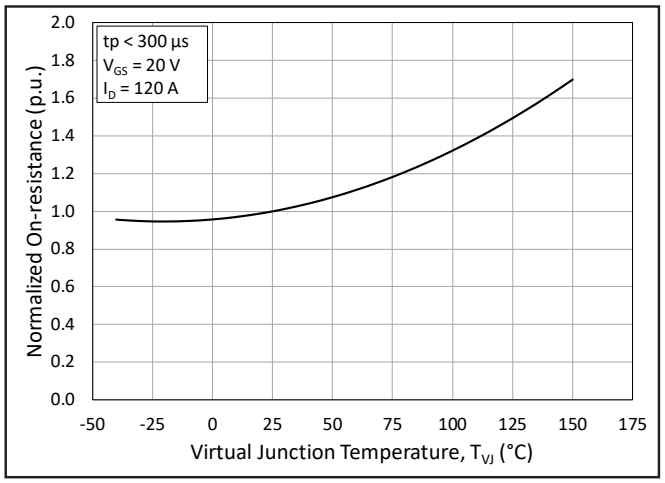


Figure 3. Normalized On-State Resistance vs. Junction Temperature

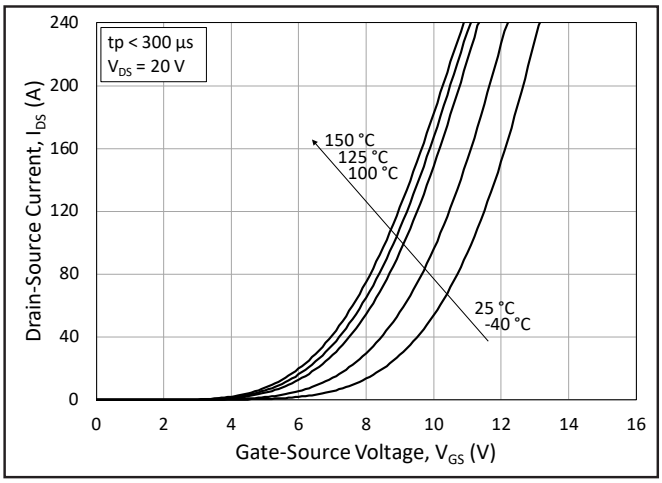


Figure 4. Transfer Characteristic for Various Junction Temperatures

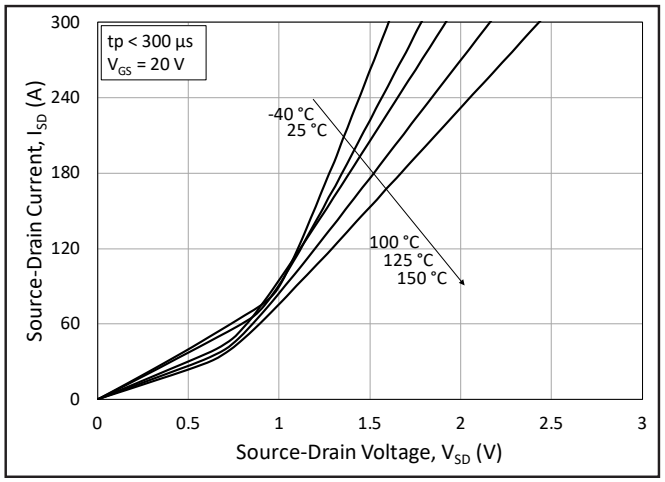


Figure 5. 3rd Quadrant Characteristic vs. Junction Temperatures at V_{GS} = 20 V (Note: 2)

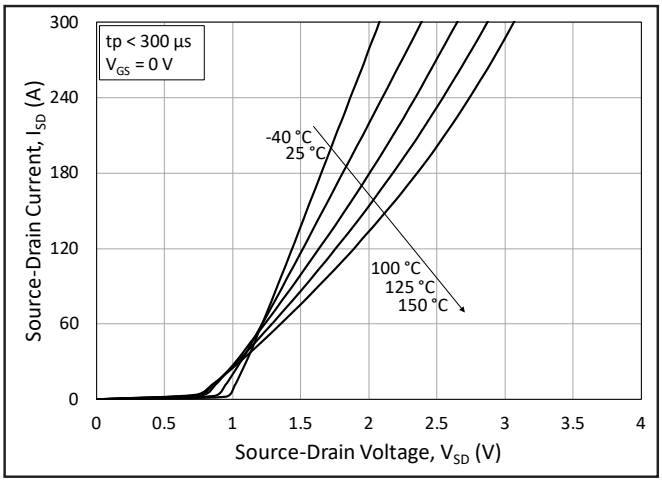


Figure 6. 3rd Quadrant Characteristic vs. Junction Temperatures at V_{GS} = 0 V (Diode) (Note: 2)

Typical Performance

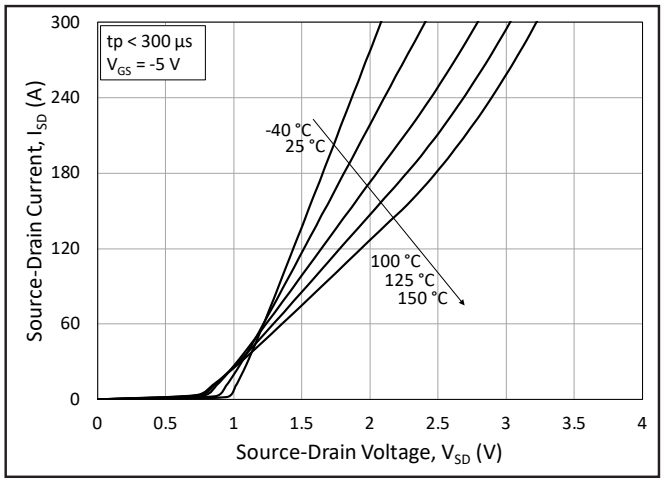


Figure 7. 3rd Quadrant Characteristic vs. Junction Temperatures at V_{GS} = -5 V (Diode) (Note: 2)

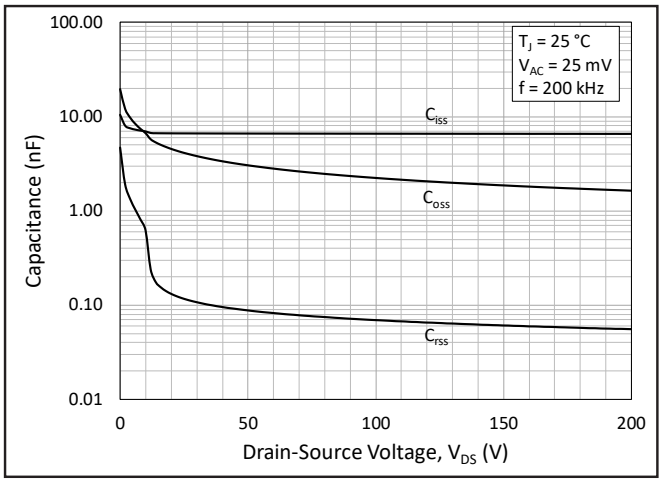


Figure 8. Typical Capacitances vs. Drain to Source Voltage (0 - 200 V)

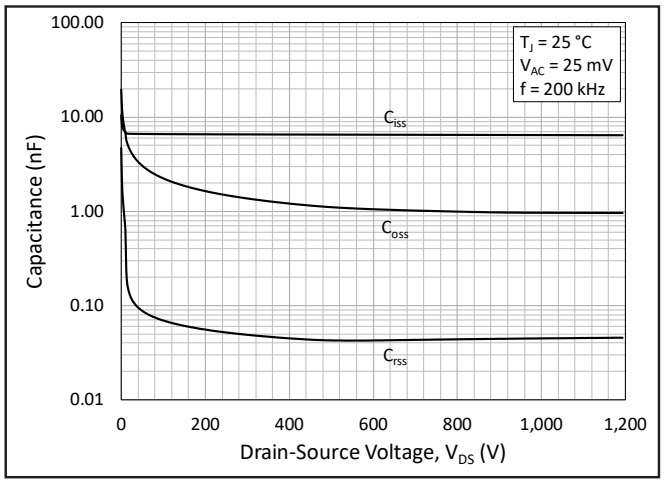


Figure 9. Typical Capacitances vs. Drain to Source Voltage (0 - 1200 V)

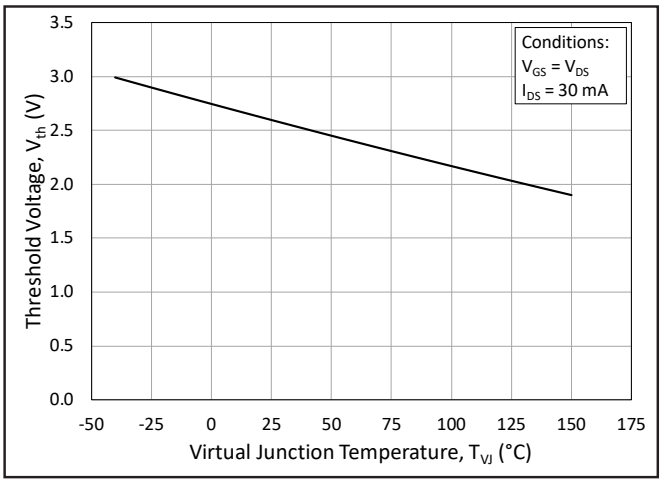


Figure 10. Threshold Voltage vs. Junction Temperature

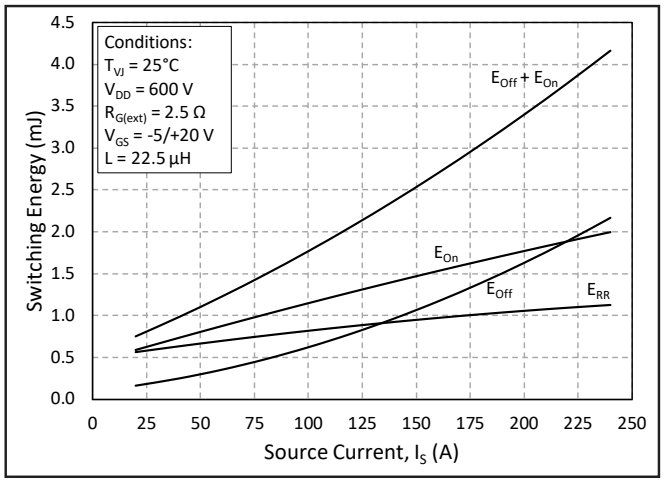


Figure 11. Switching Energy vs. Drain Current (V_{DS} = 600 V)

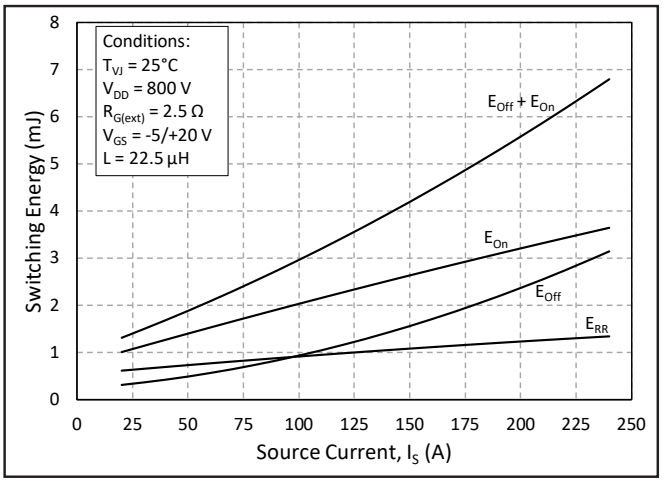


Figure 12. Switching Energy vs. Drain Current (V_{DS} = 800 V)

Typical Performance

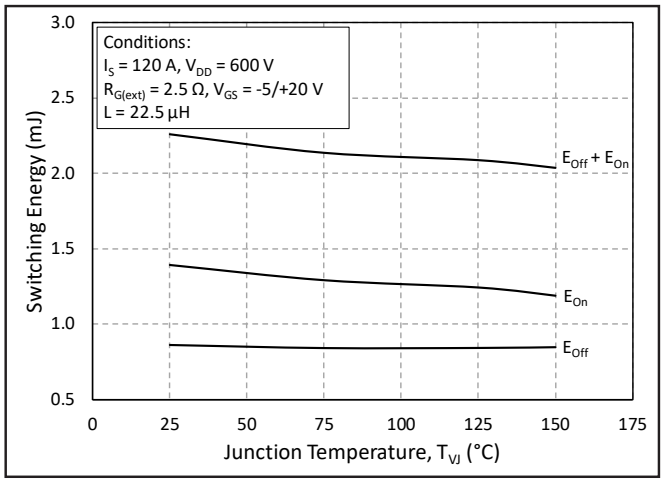


Figure 13. MOSFET Switching Energy vs. Junction Temperature

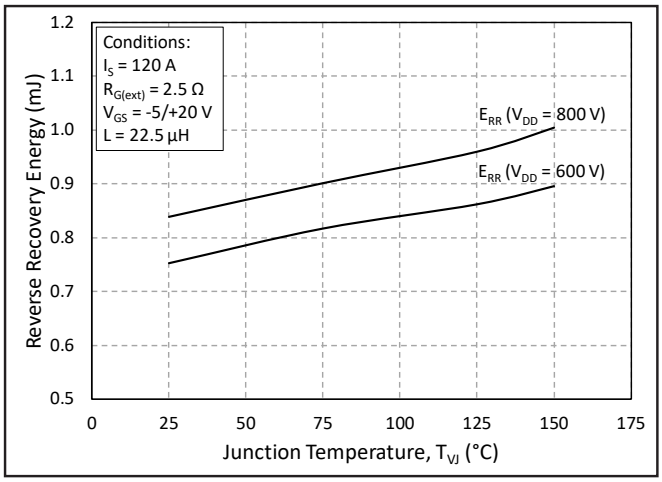


Figure 14. Reverse Recovery Energy vs. Junction Temperature (Note: 2)

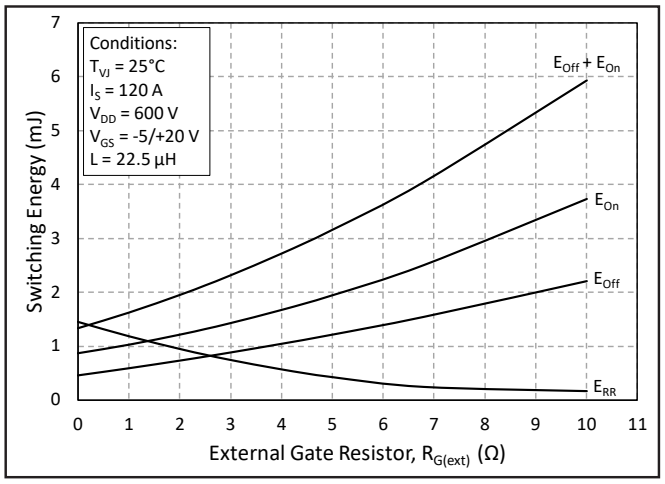


Figure 15. MOSFET Switching Energy vs. External Gate Resistance

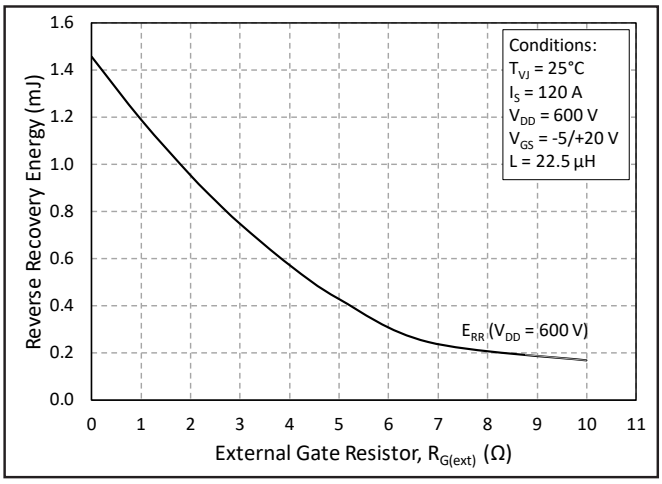


Figure 16. Reserve Recovery Energy vs. External Gate Resistance (Note: 2)

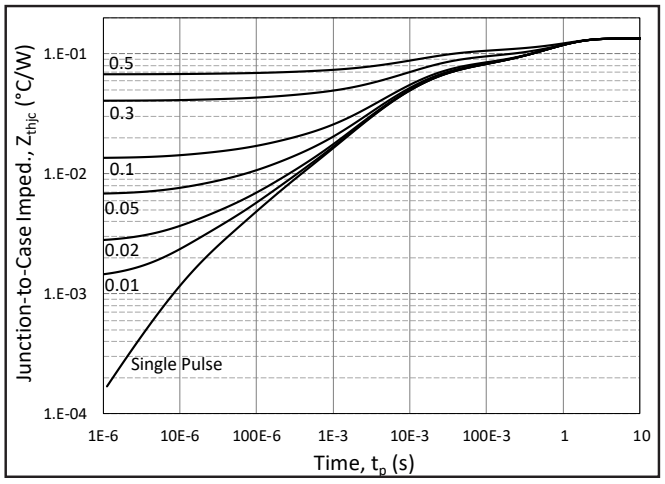


Figure 17. MOSFET Junction to Case Transient Thermal Impedance, $Z_{th\ JC}$ (°C/W)

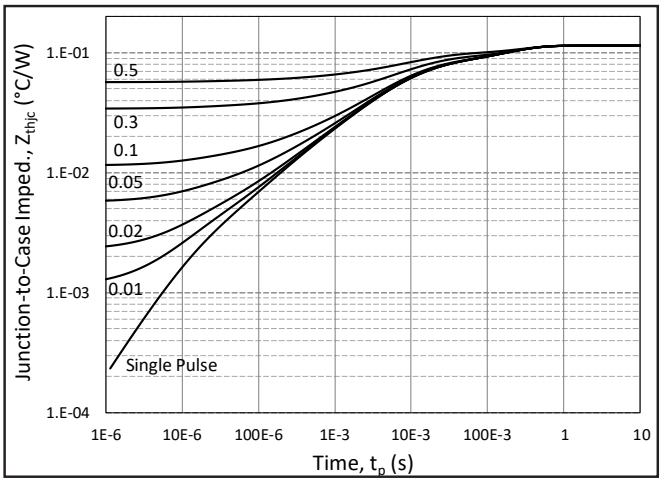


Figure 18. Diode Junction to Case Transient Thermal Impedance, $Z_{th\ JC}$ (°C/W)

Typical Performance

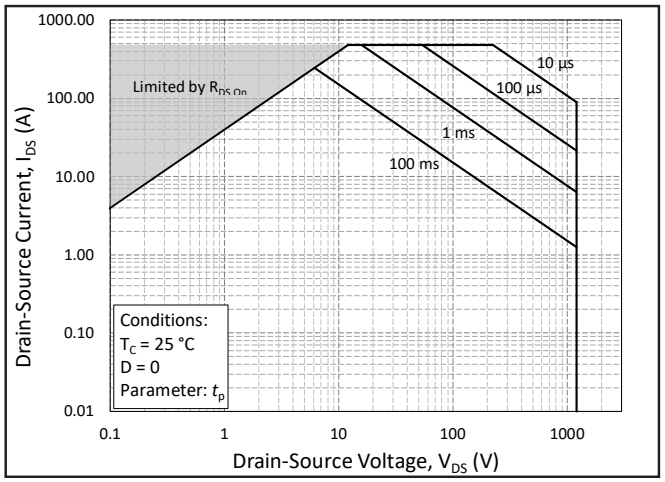


Figure 19. Forward Bias Safe Operating Area (FBSOA)

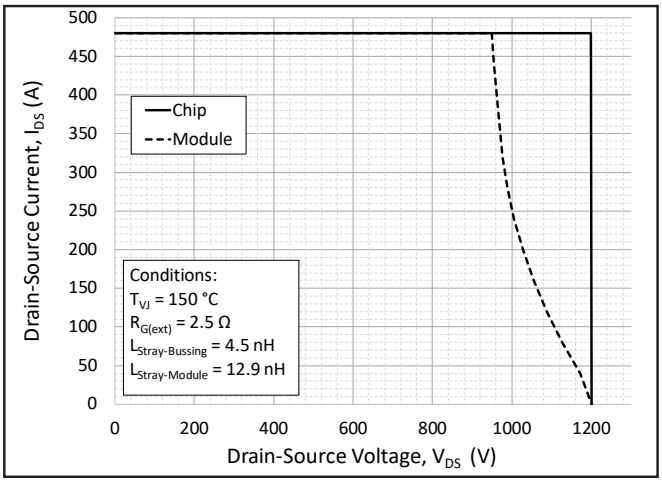


Figure 20. Reverse Bias Safe Operating Area (RBSOA)

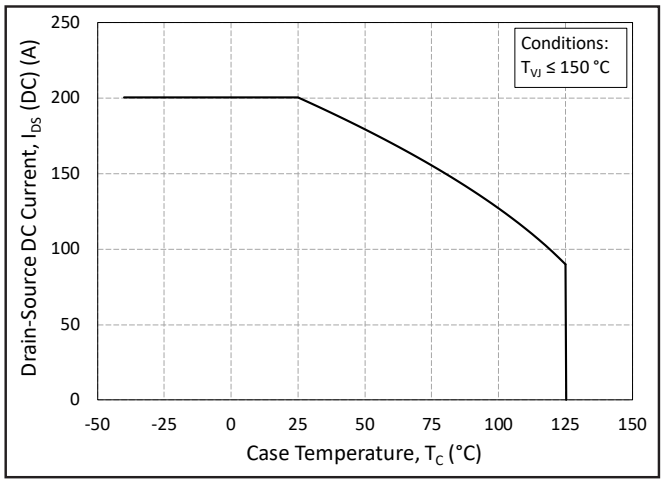


Figure 21. Continuous Drain Current Derating vs. Case Temperature

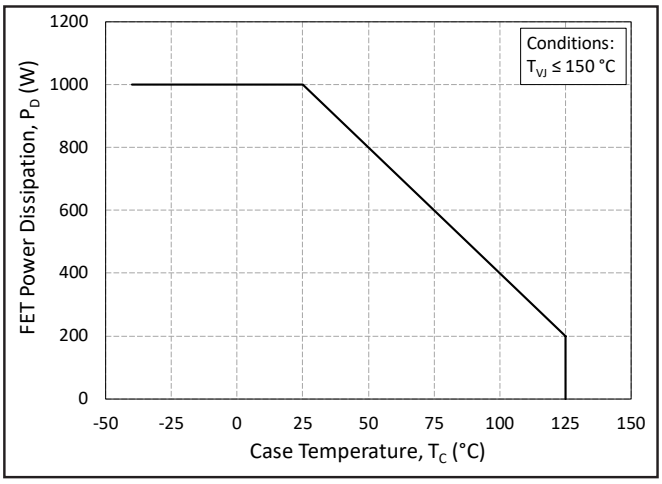


Figure 22. Maximum Power Dissipation Derating vs. Case Temperature

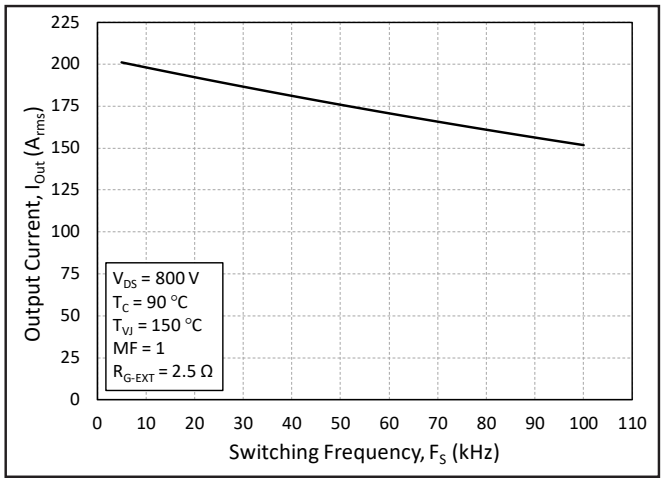


Figure 23. Typical Output Current Capability vs. Switching Frequency (Inverter Application)

Timing Characteristics

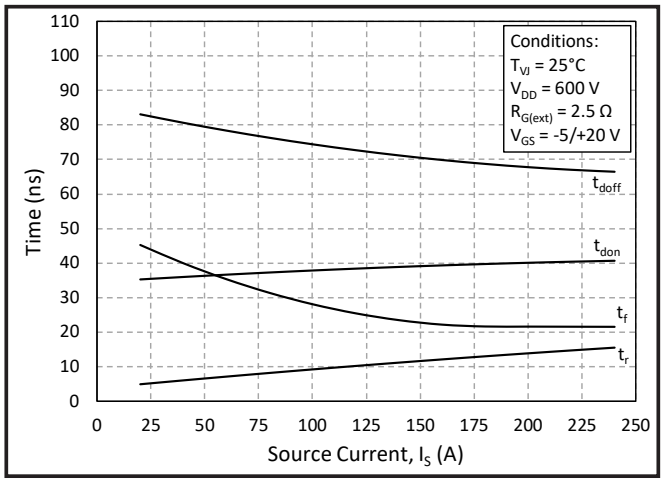


Figure 24. Timing vs. Source Current

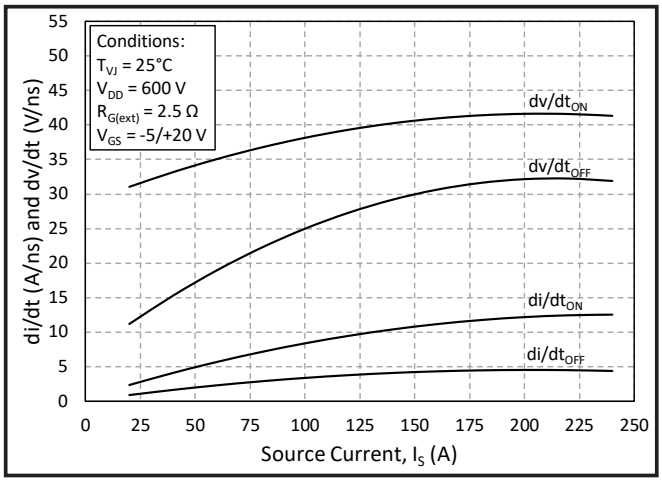


Figure 25. dv/dt and di/dt vs. Source Current

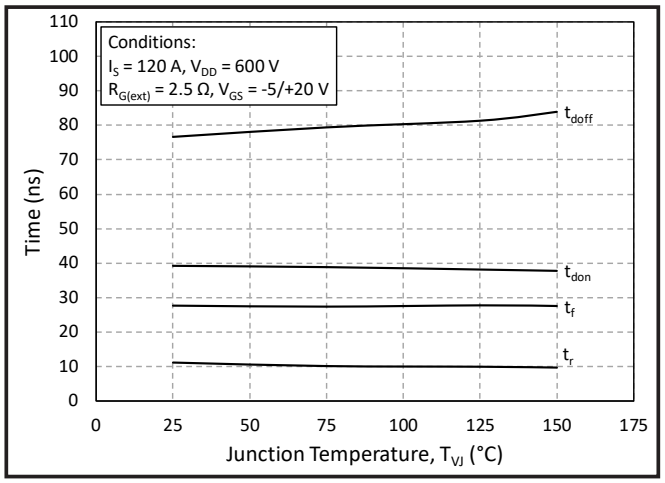


Figure 26. Timing vs. Junction Temperature

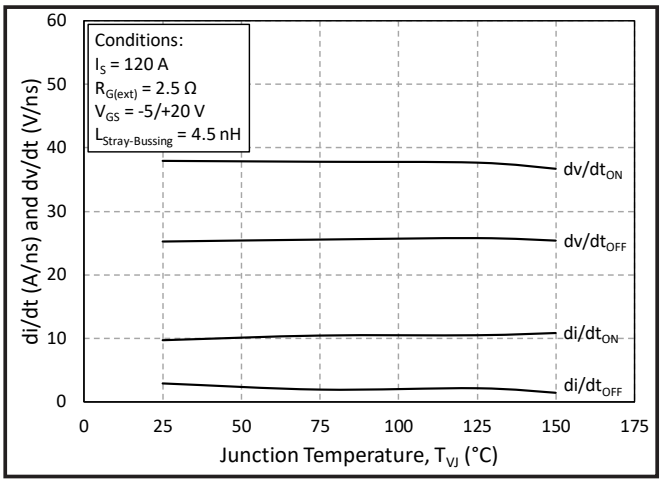


Figure 27. dv/dt and di/dt vs. Source Current

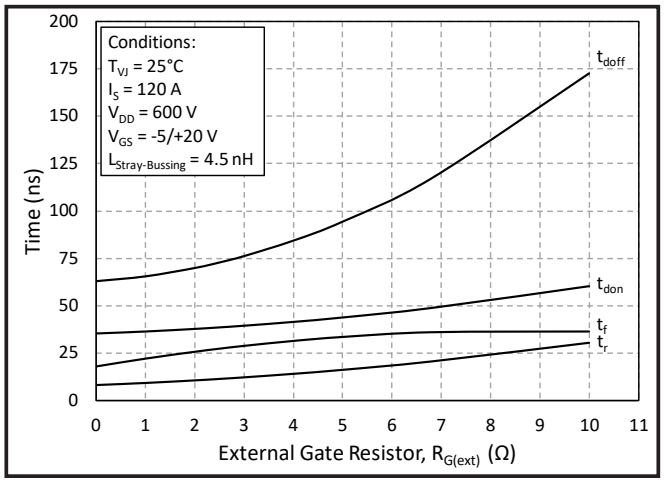


Figure 28. Timing vs. External Gate Resistance

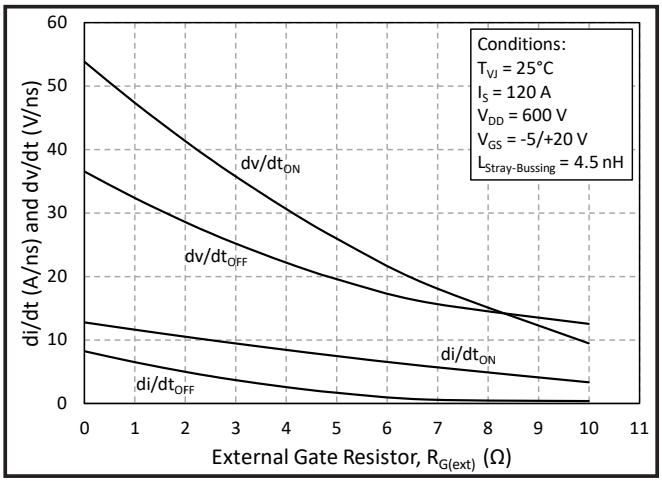


Figure 29. dv/dt and di/dt vs. External Gate Resistance

Definitions

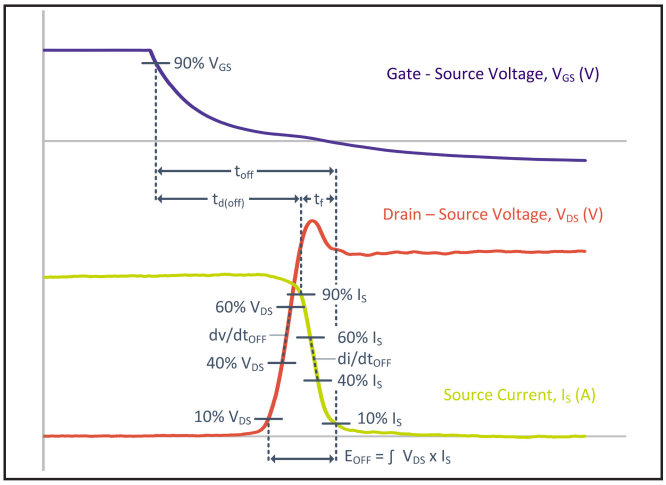


Figure 30. Turn-Off Transient Definitions

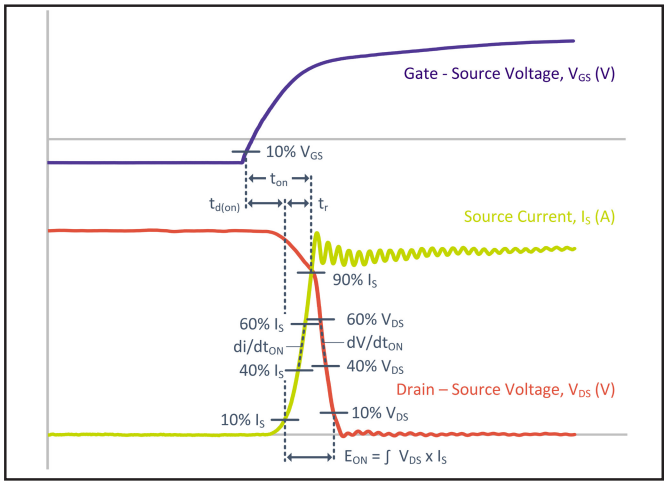


Figure 31. Turn-On Transient Definitions

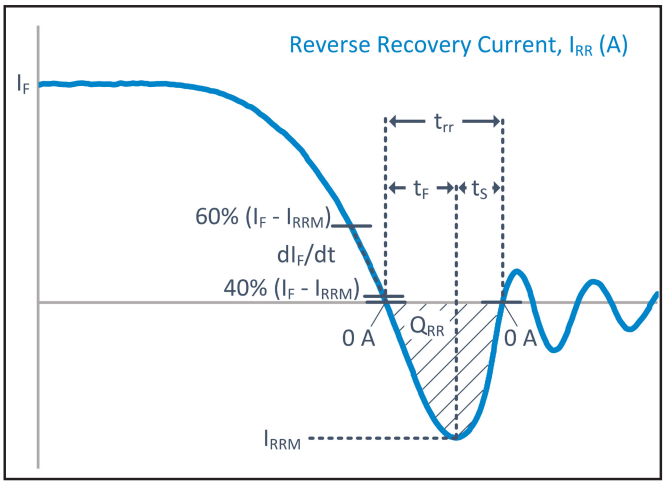


Figure 32. Reverse Recovery Definitions (Note 2)

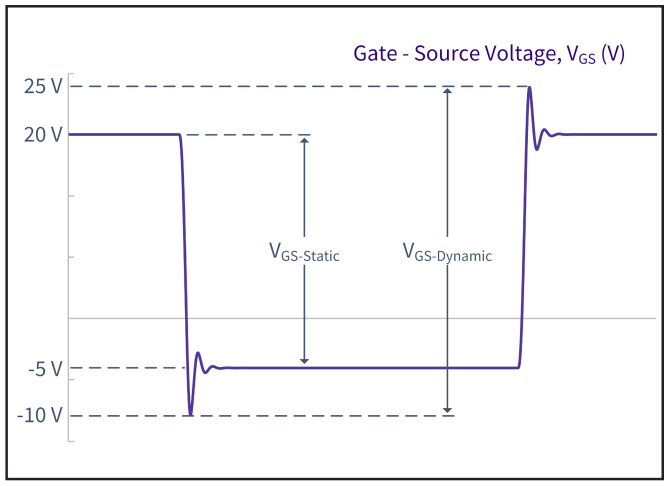
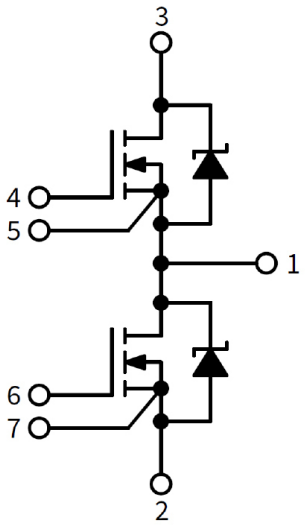
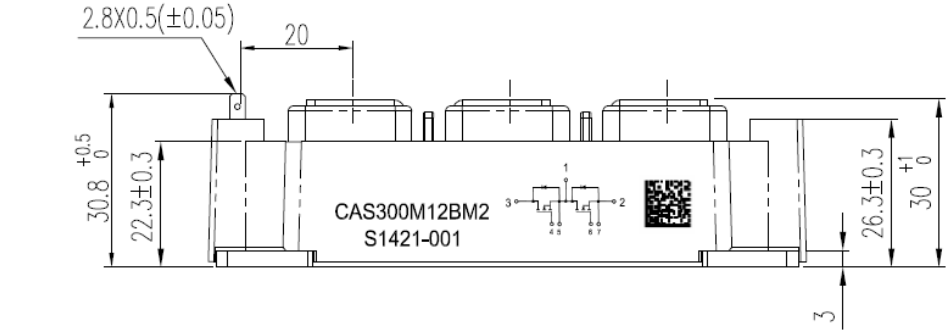


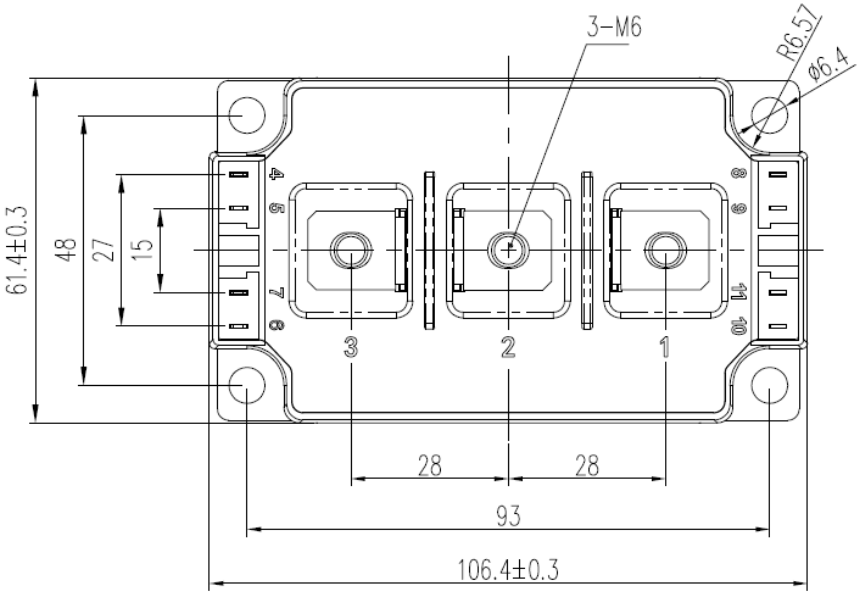
Figure 33. V_{GS} Transient Definitions

Schematic and Pin Out



Package Dimensions (mm)





Supporting Links & Tools

- CGD1200HB2P-BM2 Evaluation Gate Driver
- CGD12HB00D: Differential Transceiver Board
- KIT-CRD-CIL12N-BM: Dynamic Performance Evaluation Board for the BM2 and BM3 Module

Notes & Disclaimer

This document and the information contained herein are subject to change without notice. Any such change shall be evidenced by the publication of an updated version of this document by Wolfspeed. No communication from any employee or agent of Wolfspeed or any third party shall effect an amendment or modification of this document. No responsibility is assumed by Wolfspeed for any infringement of patents or other rights of third parties which may result from use of the information contained herein. No license is granted by implication or otherwise under any patent or patent rights of Wolfspeed.

Notwithstanding any application-specific information, guidance, assistance, or support that Wolfspeed may provide, the buyer of this product is solely responsible for determining the suitability of this product for the buyer's purposes, including without limitation for use in the applications identified in the next bullet point, and for the compliance of the buyers' products, including those that incorporate this product, with all applicable legal, regulatory, and safety-related requirements.

This product has not been designed or tested for use in, and is not intended for use in, applications in which failure of the product would reasonably be expected to cause death, personal injury, or property damage, including but not limited to equipment implanted into the human body, life-support machines, cardiac defibrillators, and similar emergency medical equipment, aircraft navigation, communication, and control systems, aircraft power and propulsion systems, air traffic control systems, and equipment used in the planning, construction, maintenance, or operation of nuclear facilities.

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfspeed representative or from the Product Documentation sections of www.wolfspeed.com.

REACh Compliance

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact your Wolfspeed representative to ensure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

Contact info:

4600 Silicon Drive
Durham, NC 27703 USA
Tel: +1.919.313.5300
www.wolfspeed.com/power

© 2024 Wolfspeed, Inc. All rights reserved. Wolfspeed® and the Wolfstreak logo are registered trademarks and the Wolfspeed logo is a trademark of Wolfspeed, Inc.
The information in this document is subject to change without notice.

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

- View CAS120M12BM2 on WIN SOURCE
- Cree/Wolfspeed Information

Optimize Your Supply Chain with WIN SOURCE Solutions

- Global Sourcing Solution
- Obsolete Management
- Cost Control Management
- Shortage Management
- Alternative Solution
- Excess Inventory Management